

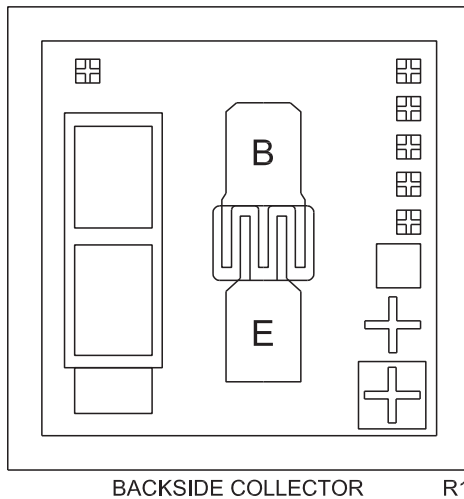
PROCESS CP317V
Small Signal Transistor
 NPN - RF Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.5 x 14.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	2.4 x 2.2 MILS
Emitter Bonding Pad Area	2.4 x 2.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

53,788

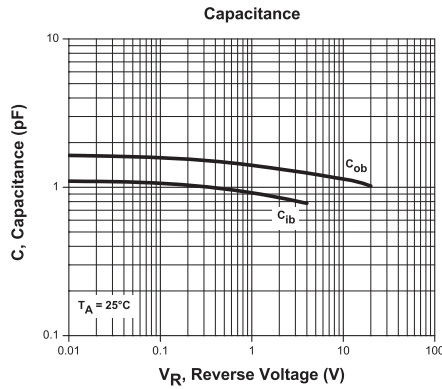
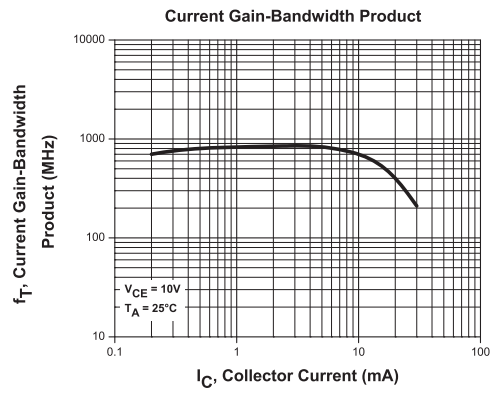
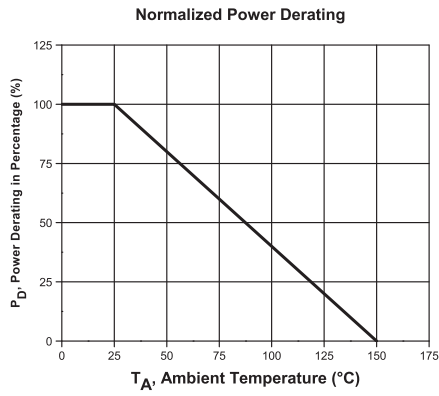
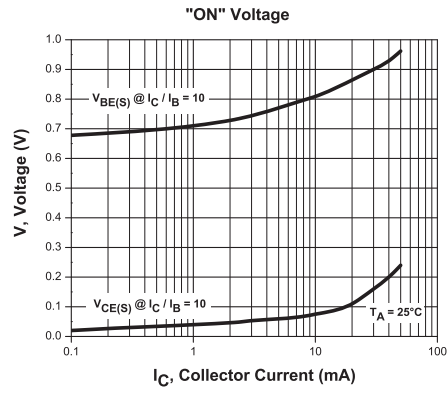
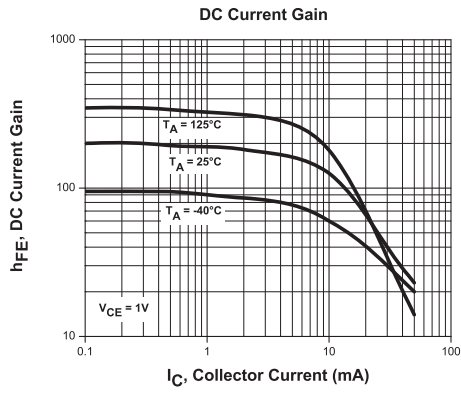
PRINCIPAL DEVICE TYPES

- CMPT918
- 2N918
- 2N2857
- 2N5179
- 2N5770
- BFY90
- PN3563
- PN3564

R0 (30-August 2011)

PROCESS CP317V

Typical Electrical Characteristics



R0 (30-August 2011)